#### SILICON EPITAXIAL PLANAR DIODE

#### **Features**

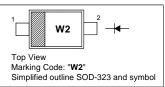
- · Low forward voltage
- Fast Reverse Recovery Time
- Small Total Capacitance

### **Application**

• Ultra high speed switching

#### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



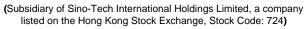
#### Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	$V_{RM}$	85	V
Reverse Voltage	$V_R$	80	V
Average Forward Current	Io	100	mA
Maximum (Peak) Forward Current	I <sub>FM</sub>	200	mA
Surge Forward Current (10 ms)	I <sub>FSM</sub>	1	А
Power Dissipation	P <sub>tot</sub>	200	mW
Junction Temperature	T <sub>j</sub>	125	°C
Storage Temperature Range	T <sub>stg</sub>	- 55 to + 125	°C

# Characteristics at T<sub>a</sub> = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I <sub>F</sub> = 100 mA	V <sub>F</sub>	1.2	V
Reverse Current at $V_R = 30 \text{ V}$ at $V_R = 80 \text{ V}$	I <sub>R</sub>	0.1 0.5	μΑ
Total Capacitance at f = 1 MHz	Ст	3	pF
Reverse Recovery Time at I <sub>F</sub> = 10 mA	t <sub>rr</sub>	4	ns







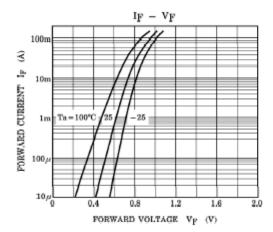


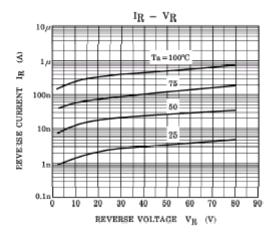


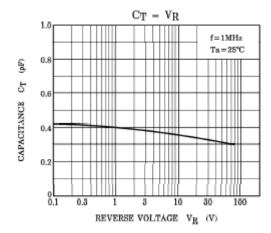




Dated: 07/04/2009

















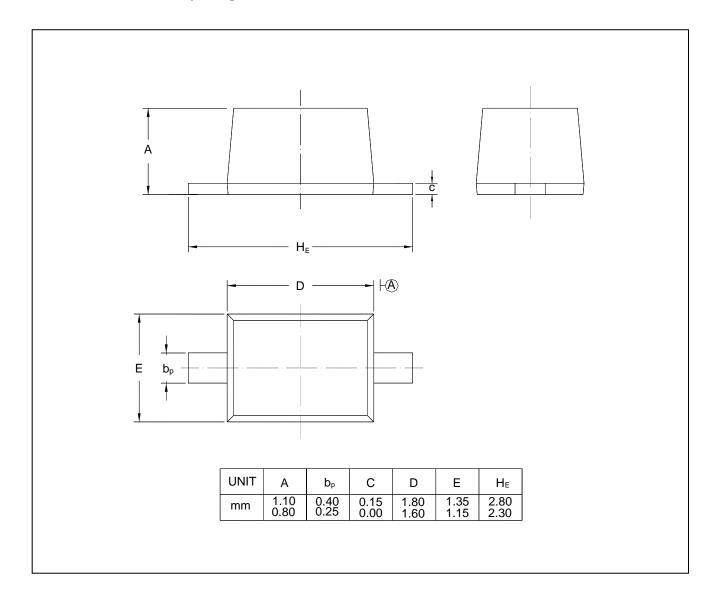




# **PACKAGE OUTLINE**

Plastic surface mounted package; 2 leads

**SOD-323** 



# SEMTECH ELECTRONICS LTD.









